EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"7237332".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 07:59
L2	2	"5049221".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:11
L3	0	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric) and pressuriz$4 and (b near stage) and (plating or electroplating) same conductor and 438/624.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:22
L4	7	438/624.ccls. and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:22
L5	7	438/624.ccls. and (b near stage) and (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:23
L6	1	438/624.ccls. and (b near stage) and (substrate or wafer or carrier or base or plate) and thermo	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:35

L7	2	"5480048".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:38
S1	0	(("JP2001-537286") or ("JP2001-68850") or ("JP7-111375") or ("JP6-350258") or ("JP10-022636") or ("JP2002-137328") or ("JP2002-134881") or ("JP2002-076578")). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/26 09:27
S2	37	"5600103"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S3	172	"power supply film"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S4	1	"power supply film" and insulat$4 and conduct$4 and "b-stage"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S5	4	"power supply film" and insulat$4 and conduct$4 and thermoset$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S6	3	"power supply film" and insulat$4 and conduct$4 and thermoset$4 and curing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S7	4	"power supply film" and insulat$4 and conduct$4 and thermoset$4 and cur$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S8	623590	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:43

S9	239119	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and (((insulat$4 or oxide or dielectric) near9 conduct$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:44
S10	16737	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and (((insulat$4 or oxide or dielectric) near9 conduct$4) and (press $3 near9 (oxide or dielectric insulat$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:47
S11	381	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and (((insulat$4 or oxide or dielectric) near9 conduct$4) and (press $3 near9 (oxide or dielectric insulat$4)) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:48
S12	52	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and (((insulat$4 or oxide or dielectric) near9 conduct$4) and (press $3 near9 (oxide or dielectric insulat$4)) and (b near stage) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:45
S13	27	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and (((insulat$4 or oxide or dielectric) near9 conduct$4) and (press $3 near9 (oxide or dielectric insulat$4)) and (b near stage) and (power near supply) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:50

S14	11	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (press $3 near9 (oxide or dielectric insulat$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:12
S15	3	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:13
S16	1982	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
S17	937	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4)) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14

S18	86	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4)) and (support or frame) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:15
S19	81	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4)) and (support or frame) and (b near stage) and ((heat$4 or thermal) near9 (oxide or dielectric or insulat $4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/06 09:57
S20	3	(conduct$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat$4 or oxide or dielectric) near9 conduct$4) and (pressing near9 (oxide or dielectric insulat$4)) and (support or frame) and (b near stage) and ((heat$4 or thermal) near9 (oxide or dielectric or insulat $4)) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:21
S21	128560	(conduct$4 near9 (plating or etch$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:37

S22	111747	(conduct$4 near9 (plating or etch$4)) and (support or base pr carrier or arm or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:38
S23	35038	(conduct$4 near9 (plating or etch$4)) and (support or base pr carrier or arm or substrate or wafer) and press$4 and (insulat$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:40
S24	7011	(conduct$4 near9 (plating or etch$4)) and (support or base pr carrier or arm or substrate or wafer) and press$4 and (insulat$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer) and (press$4 near9 (insulat$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:41
S25	7010	(conduct$4 near9 (plating or etch$4)) and (support or base or carrier or arm or substrate or wafer) and press$4 and (insulat$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press$4 near9 (insulat$4 or dielectric or oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:42

S26	338	(conduct$4 near9 (plating or etch$4)) and (support or base or carrier or arm or substrate or wafer) and press$4 and (insulat$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press$4 near9 (insulat$4 or dielectric or oxide)) and (electronic near part)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:44
S27	46	(conduct$4 near9 (plating or etch$4)) and (support or base or carrier or arm or substrate or wafer) and press$4 and (insulat$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press$4 near9 (insulat$4 or dielectric or oxide)) and (electronic near part) and (B near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 15:01
S28	88010	(conduct$4 near portion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 09:55
S29	12774	(conduct$4 near portion) near9 (support or base or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:52
S30	1242	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54

S31	55	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric)) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54
S32	46	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric)) and (b near stage) and press $4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:55
S33	27	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric)) and (b near stage) and press $4 and thermoplastic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
S34	25	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric)) and (b near stage) and press $4 and thermoplastic and (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
S35	9	(conduct$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat$4 or oxide or dielectric)) and (b near stage) and press $4 and thermoplastic and (heat or anneal) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56

S36	7	("5480048" | "5600103" | "5970319" | "6930388").PN. and (conduct$4 or metal) with (substrate or wafer or carrier or base or plate or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:30
S37	2	("5480048" | "5600103" | "5970319" | "6930388").PN. and (conduct$4 or metal) with (substrate or wafer or carrier or base or plate or support) and (insulat$4 or oxide or dielectric) and press$4 with (insulat$4 or oxide or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:32
S38	380505	(support or wafer or carrier or substrate or base) same conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:52
S39	4336	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:53
S40	1442	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:54

S41	1137	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:56
S42	118	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric) and pressuriz$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:04
S43	56	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric) and pressuriz$4 and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:04
S44	49	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric) and pressuriz$4 and (b near stage) and (plating or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:05

		electroplating)				
S45	23	(support or wafer or carrier or substrate or base) same conductor and (insulat$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press$4 same ((copper or "Cu") near foil)) same (insulat$4 or oxide or dielectric) and pressuriz$4 and (b near stage) and (plating or electroplating) same conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:05

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